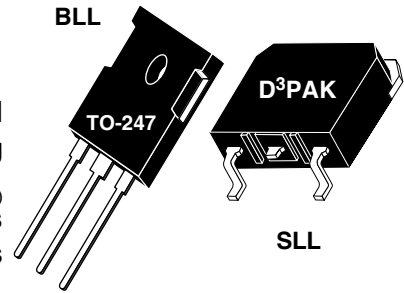
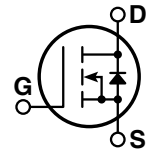


## POWER MOS 7® MOSFET

Power MOS 7® is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETS. Both conduction and switching losses are addressed with Power MOS 7® by significantly lowering  $R_{DS(ON)}$  and  $Q_g$ . Power MOS 7® combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.



- Lower Input Capacitance
- Lower Miller Capacitance
- Lower Gate Charge,  $Q_g$
- Increased Power Dissipation
- Easier To Drive
- TO-247 or Surface Mount D<sup>3</sup>PAK Package




### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT5024BLL_SLL(G)	UNIT
$V_{DSS}$	Drain-Source Voltage	500	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	22	Amps
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	88	
$V_{GS}$	Gate-Source Voltage Continuous	$\pm 30$	Volts
$V_{GSM}$	Gate-Source Voltage Transient	$\pm 40$	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	265	Watts
	Linear Derating Factor	2.12	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300	
$I_{AR}$	Avalanche Current <sup>①</sup> (Repetitive and Non-Repetitive)	22	Amps
$E_{AR}$	Repetitive Avalanche Energy <sup>①</sup>	30	mJ
$E_{AS}$	Single Pulse Avalanche Energy <sup>④</sup>	960	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu\text{A}$ )	500			Volts
$I_{D(on)}$	On State Drain Current <sup>②</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ )	22			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10V, I_D = 11A$ )			0.24	Ohms
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = 500V, V_{GS} = 0V$ )			100	$\mu\text{A}$
	Zero Gate Voltage Drain Current ( $V_{DS} = 400V, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )			500	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 1mA$ )	3		5	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

**DYNAMIC CHARACTERISTICS**

**APT5024BLL\_SLL(G)**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1 MHz		1900		pF
C <sub>oss</sub>	Output Capacitance			417		
C <sub>rss</sub>	Reverse Transfer Capacitance			27		
Q <sub>g</sub>	Total Gate Charge ③	V <sub>GS</sub> = 10V V <sub>DD</sub> = 250V I <sub>D</sub> = 22A @ 25°C		43		nC
Q <sub>gs</sub>	Gate-Source Charge			12		
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge			24		
t <sub>d(on)</sub>	Turn-on Delay Time	<b>RESISTIVE SWITCHING</b> V <sub>GS</sub> = 15V V <sub>DD</sub> = 250V I <sub>D</sub> = 22A @ 25°C R <sub>G</sub> = 1.6Ω		8		ns
t <sub>r</sub>	Rise Time			6		
t <sub>d(off)</sub>	Turn-off Delay Time			18		
t <sub>f</sub>	Fall Time			2		
E <sub>on</sub>	Turn-on Switching Energy ⑥	<b>INDUCTIVE SWITCHING @ 25°C</b> V <sub>DD</sub> = 333V, V <sub>GS</sub> = 15V I <sub>D</sub> = 22A, R <sub>G</sub> = 5Ω		167		μJ
E <sub>off</sub>	Turn-off Switching Energy			86		
E <sub>on</sub>	Turn-on Switching Energy ⑥	<b>INDUCTIVE SWITCHING @ 125°C</b> V <sub>DD</sub> = 333V V <sub>GS</sub> = 15V I <sub>D</sub> = 22A, R <sub>G</sub> = 5Ω		262		
E <sub>off</sub>	Turn-off Switching Energy			99		

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

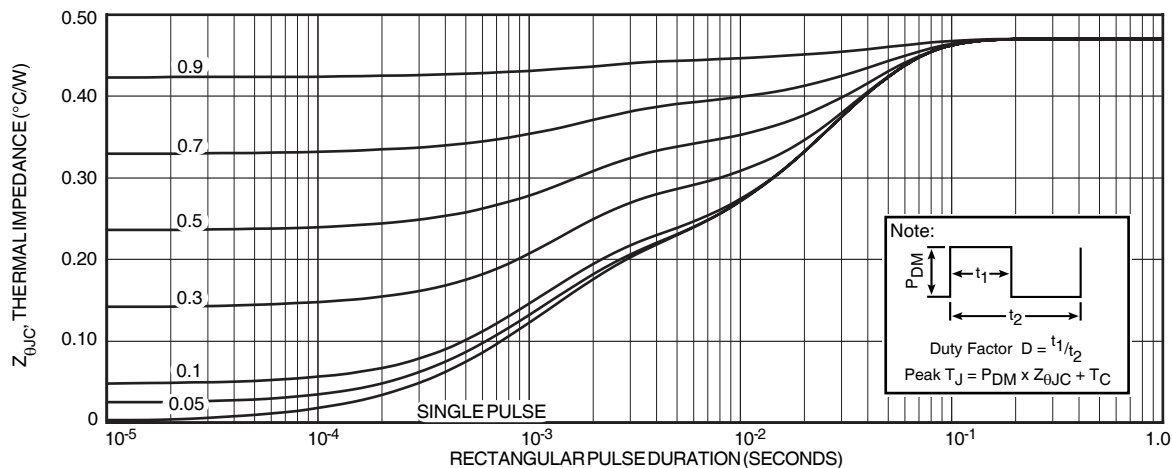
Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I <sub>S</sub>	Continuous Source Current (Body Diode)			22	Amps
I <sub>SM</sub>	Pulsed Source Current ① (Body Diode)			88	
V <sub>SD</sub>	Diode Forward Voltage ② (V <sub>GS</sub> = 0V, I <sub>S</sub> = -I <sub>D</sub> 22A)			1.3	Volts
t <sub>rr</sub>	Reverse Recovery Time (I <sub>S</sub> = -I <sub>D</sub> 22A, di <sub>S</sub> /dt = 100A/μs)		516		ns
Q <sub>rr</sub>	Reverse Recovery Charge (I <sub>S</sub> = -I <sub>D</sub> 22A, di <sub>S</sub> /dt = 100A/μs)		7		μC
dv/dt	Peak Diode Recovery dv/dt ⑤			8	V/ns

**THERMAL CHARACTERISTICS**

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R <sub>θJC</sub>	Junction to Case			0.47	°C/W
R <sub>θJA</sub>	Junction to Ambient			40	

- ① Repetitive Rating: Pulse width limited by maximum junction temperature
- ② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%
- ③ See MIL-STD-750 Method 3471
- ④ Starting T<sub>J</sub> = +25°C, L = 3.97mH, R<sub>G</sub> = 25Ω, Peak I<sub>L</sub> = 22A
- ⑤ dv/dt numbers reflect the limitations of the test circuit rather than the device itself. I<sub>S</sub> ≤ -I<sub>D</sub>22A di<sub>S</sub>/dt ≤ 700A/μs V<sub>R</sub> ≤ V<sub>DSS</sub> T<sub>J</sub> ≤ 150°C
- ⑥ E<sub>on</sub> includes diode reverse recovery. See figures 18, 20.

**APT Reserves the right to change, without notice, the specifications and information contained herein.**



**FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION**

# Typical Performance Curves

APT5024BLL\_SLL(G)

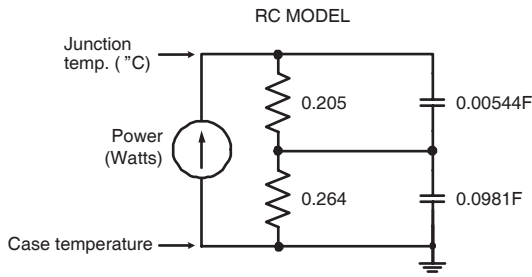


FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

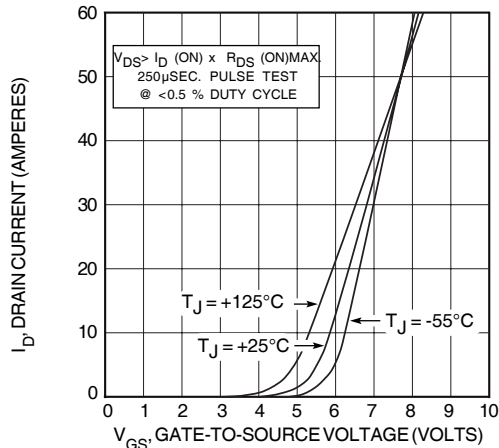


FIGURE 4, TRANSFER CHARACTERISTICS

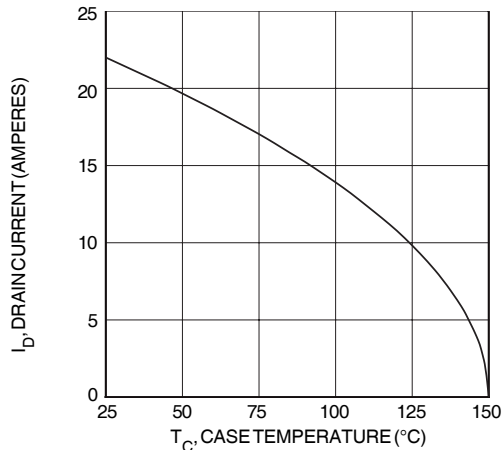


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

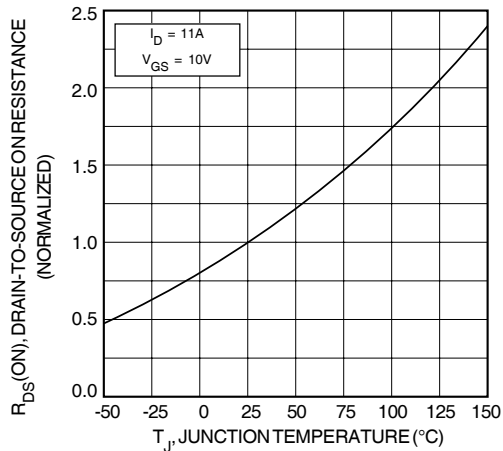


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

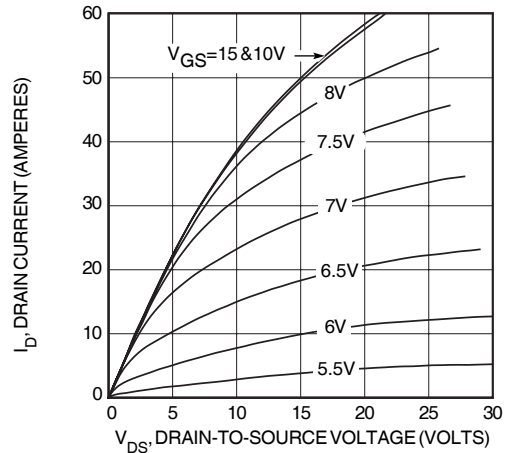


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

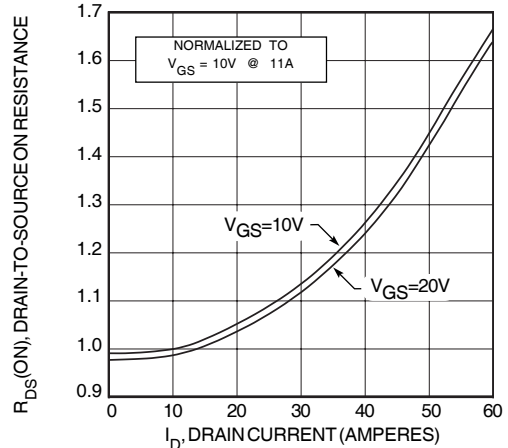


FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT

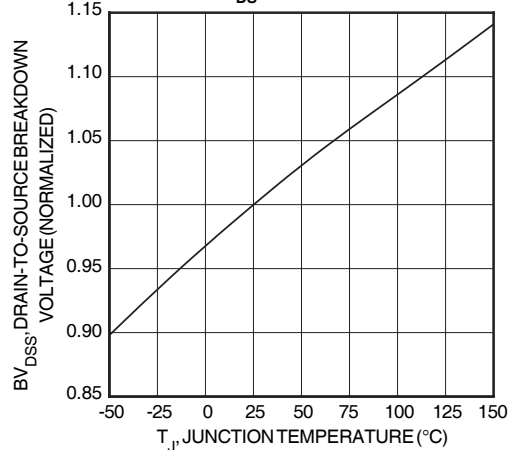


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

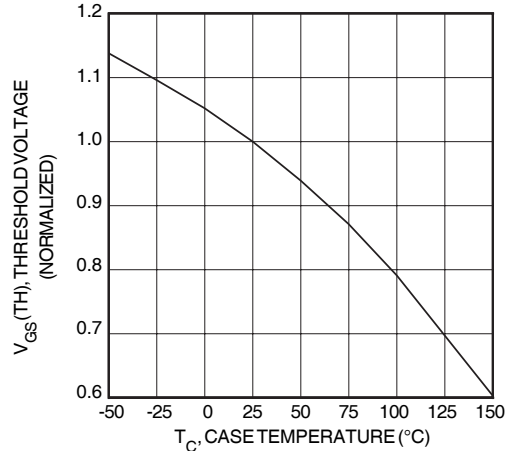


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

Typical Performance Curves

APT5024BLL\_SLL(G)

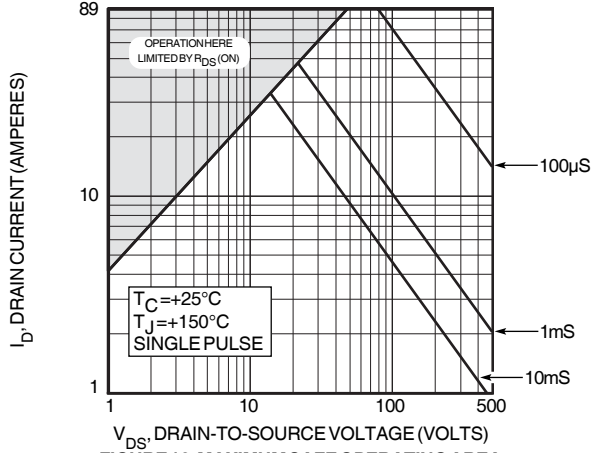


FIGURE 10, MAXIMUM SAFE OPERATING AREA

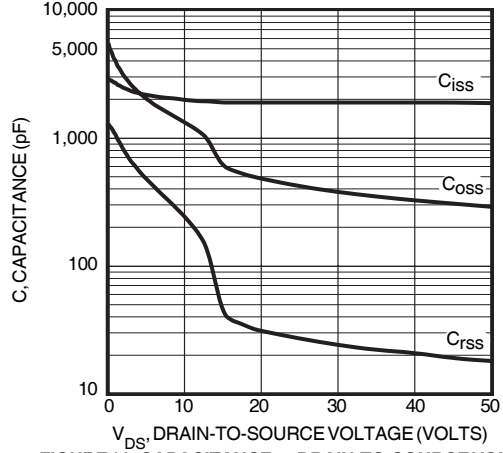


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

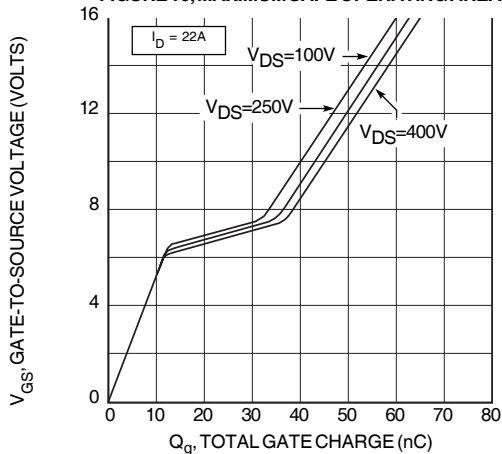


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

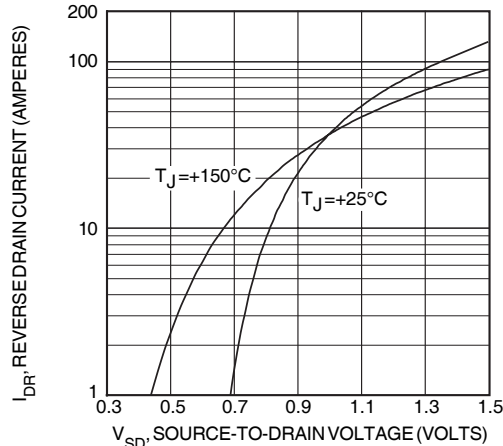


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

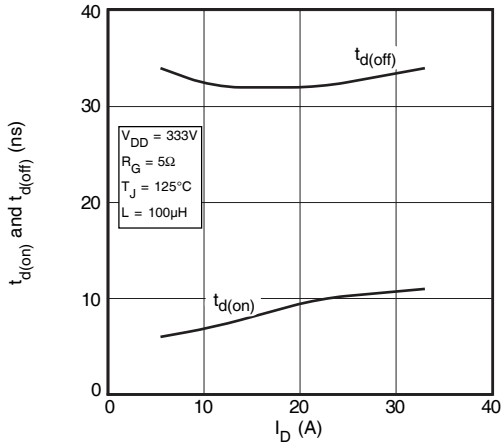


FIGURE 14, DELAY TIMES vs CURRENT

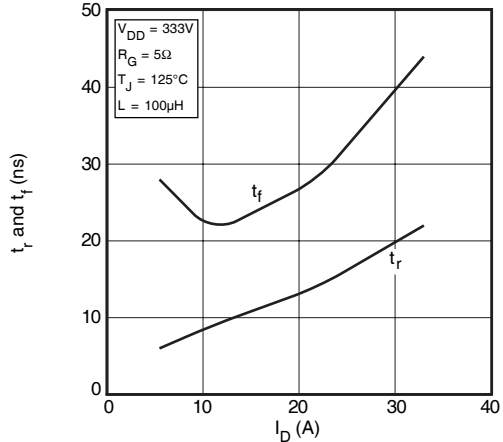


FIGURE 15, RISE AND FALL TIMES vs CURRENT

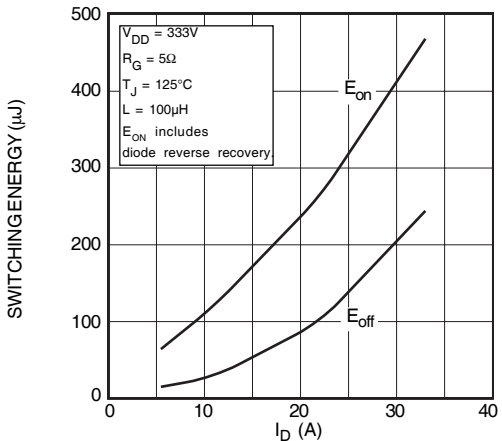


FIGURE 16, SWITCHING ENERGY vs CURRENT

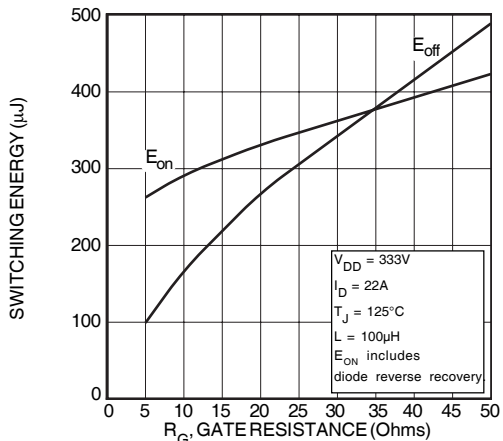


FIGURE 17, SWITCHING ENERGY vs. GATE RESISTANCE

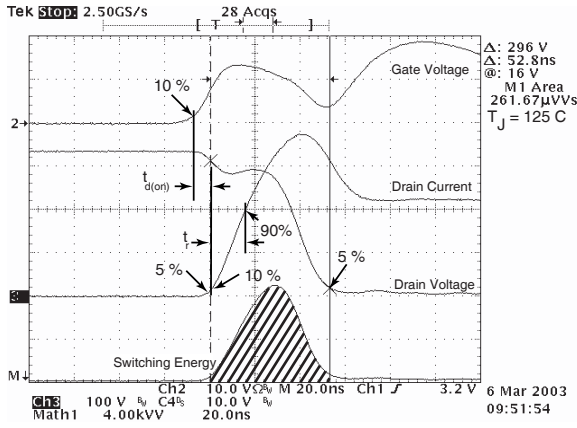


Figure 18, Turn-on Switching Waveforms and Definitions

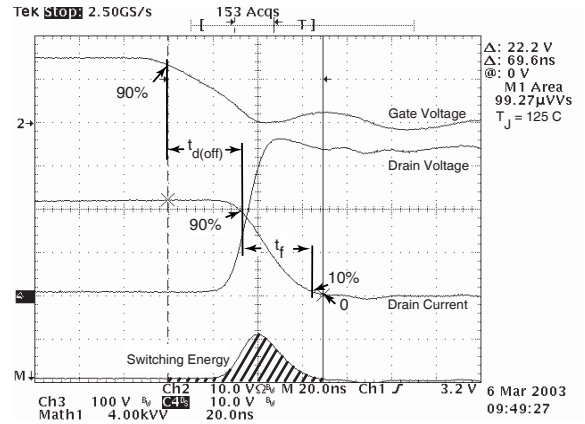


Figure 19, Turn-off Switching Waveforms and Definitions

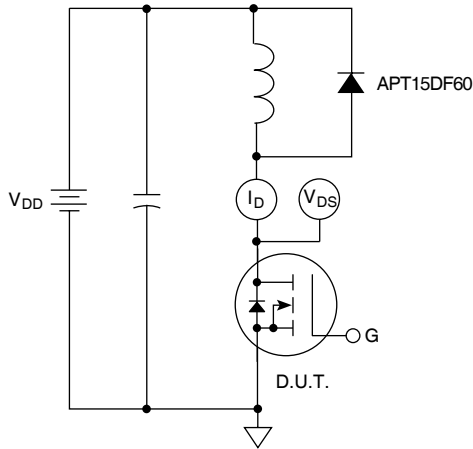
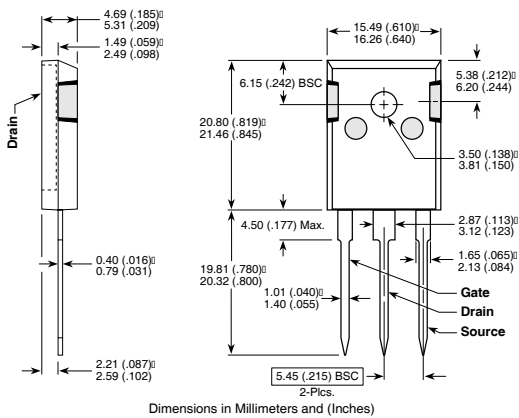


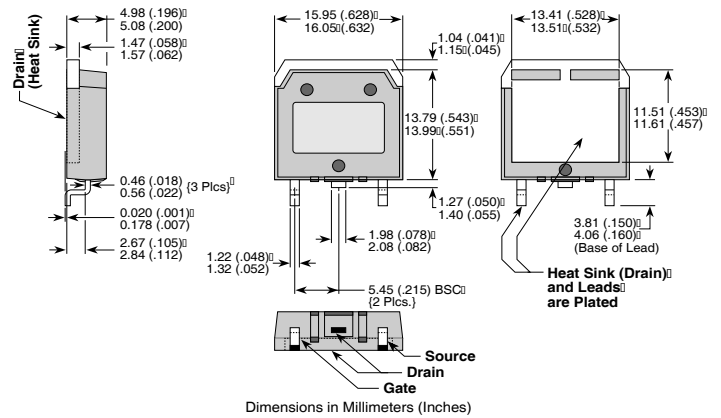
Figure 20, Inductive Switching Test Circuit

**TO-247 Package Outline**



Dimensions in Millimeters and (Inches)

**D<sup>3</sup>PAK Package Outline**



Dimensions in Millimeters (Inches)

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